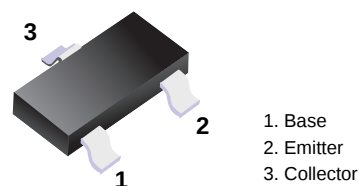


PNP Transistors

■ Features

- Complementary to MMBT3904M
- Small Package



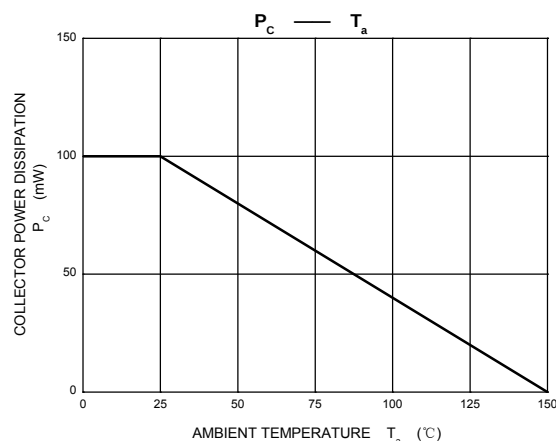
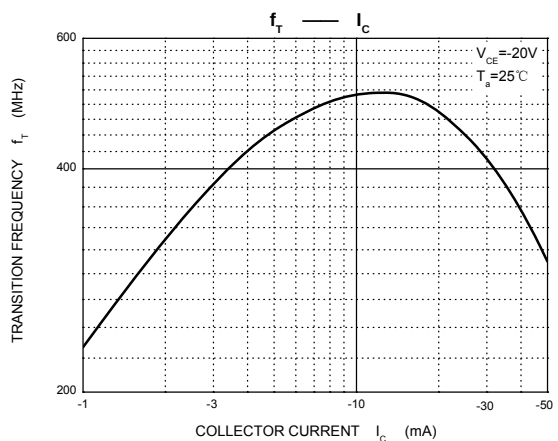
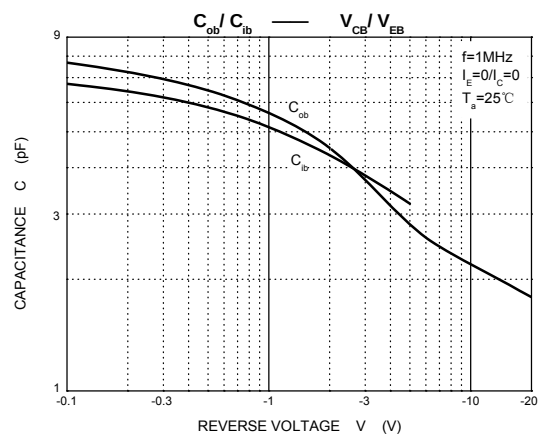
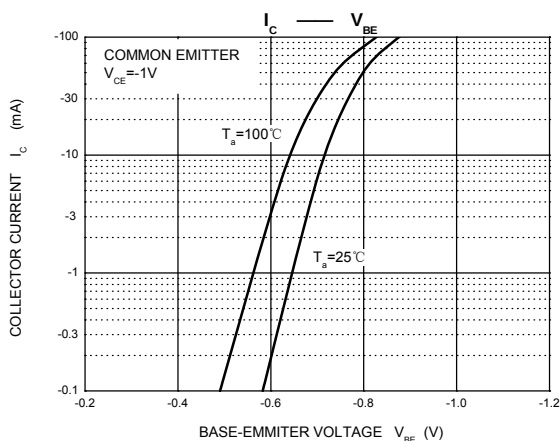
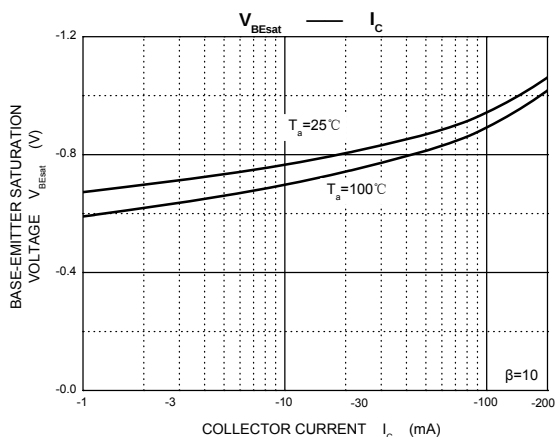
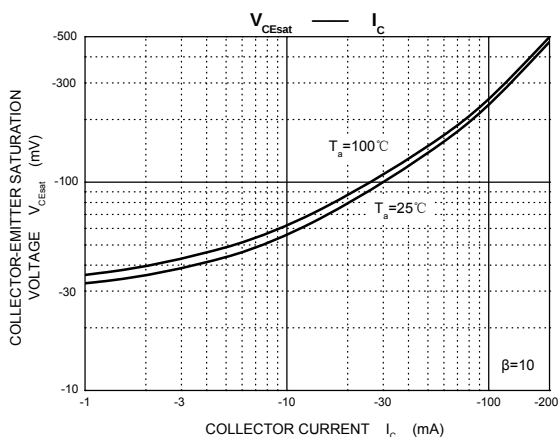
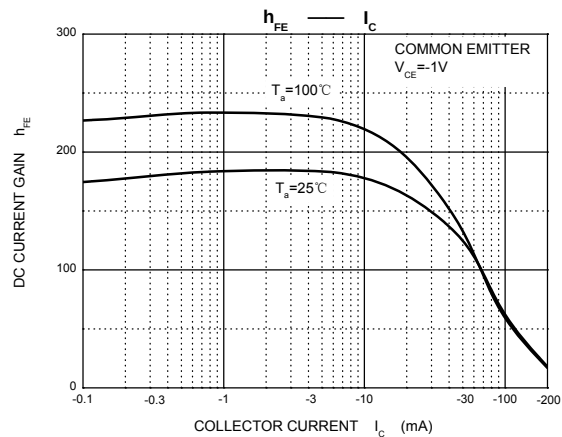
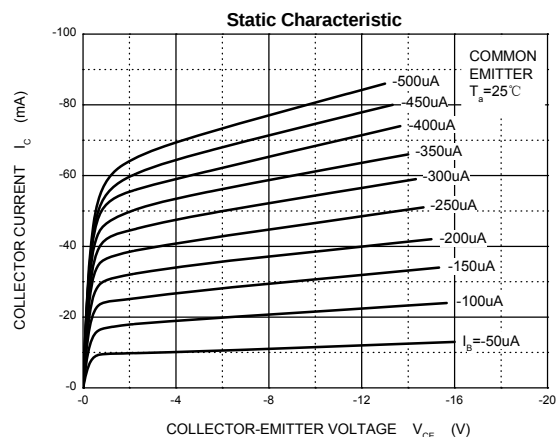
■ Simplified outline(SOT-723)

■ Absolute Maximum Ratings Ta = 25°C

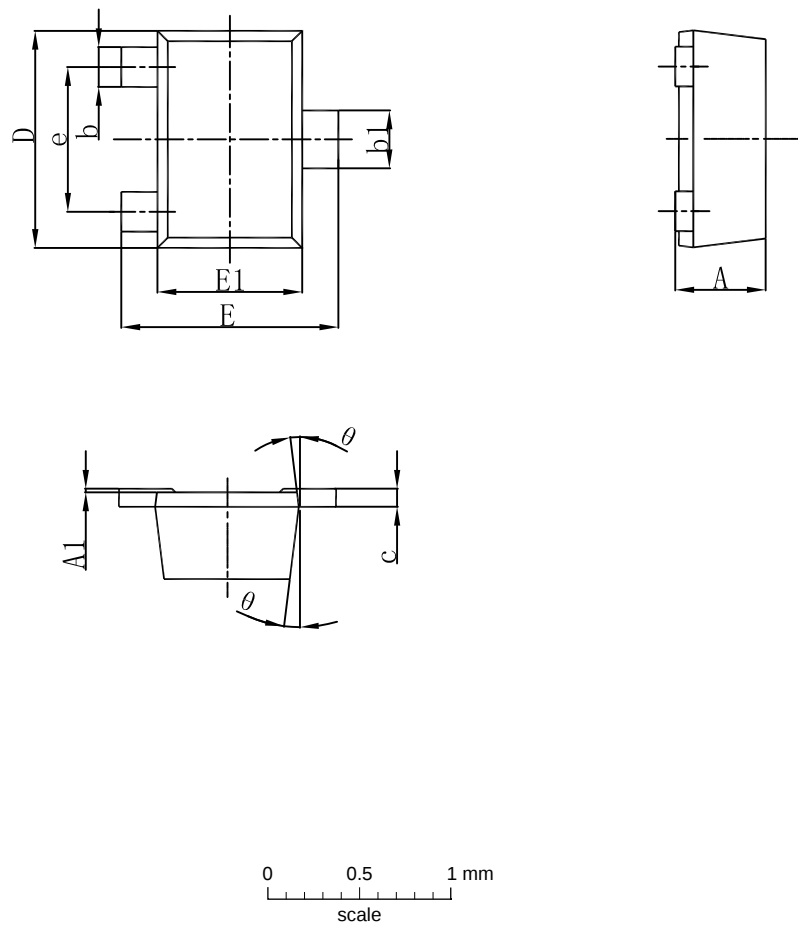
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Power Dissipation	100	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	1250	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	storage Temperature	-55~+150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{EB(off)} =-3V			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-10mA	100		300	
	h _{FE(2)}	V _{CE} =-1V, I _C =-50mA	60			
	h _{FE(3)}	V _{CE} =-2V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =-3V, V _{BE(off)} =-0.5V, I _C =-10mA, I _{B1} =I _{B2} =-1mA			35	ns
Rise time	t _r				35	ns
Storage time	t _s	V _{CC} =-3V, I _C =-10mA, I _{B1} =I _{B2} =-1mA			225	ns
Fall time	t _f				75	ns



■ SOT-723



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b	b1	c	D	E	E1
mm	0.43 0.50	0.05	0.17 0.27	0.27 0.37	0.08 0.15	1.15 1.25	0.15 0.25	0.75 0.85